

Amendments to the Claims:

A clean version of the entire set of pending claims (including amendments to the claims, if any) is submitted herewith per 37 CFR 1.121(c)(3). This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-23. (Canceled).

24. (Previously Presented) A thin film transistor (TFT), comprising:
a gate disposed on a substrate, the gate having side edges inclined towards one another to reach a tip having a radius of a few nanometers,
a gate insulating layer disposed on the gate;
a channel region disposed on the gate insulating layer;
a source electrode overlying a first side edge of the gate, and
a drain electrode overlying a second side edge of the gate.

25. (Previously Presented) The TFT of claim 24, further comprising a layer of doped semiconductor material overlying the channel region.

26. (Previously Presented) The TFT of claim 24, wherein the channel region has a length of 20-40 nanometers.

27. (Previously Presented) The TFT of claim 24, further comprising an insulating material disposed between the gate and the substrate.

28. (Previously Presented) The TFT of claim 24, wherein the channel region comprises intrinsic amorphous silicon.